

CDM22012-800LRFP

N-CHANNEL
LR POWER MOSFET
12 AMP, 800 VOLT



TO-220FP CASE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CDM22012-800LRFP is an 800 volt N-Channel MOSFET designed for high voltage, fast switching applications such as Power Factor Correction (PFC), lighting and power inverters. This MOSFET combines high voltage capability with ultra low $r_{DS(ON)}$, low threshold voltage, and low gate charge for optimal efficiency.

MARKING CODE: CDM12-800LR

APPLICATIONS:

- Power Factor Correction
- Alternative energy inverters
- Solid State Lighting (SSL)

FEATURES:

- High voltage capability ($V_{DS}=800V$)
- Low gate charge ($Q_{gs}=7.6nC$ TYP)
- Ultra low $r_{DS(ON)}$ (0.37Ω TYP)

MAXIMUM RATINGS: ($T_C=25^\circ C$ unless otherwise noted)

	SYMBOL		UNITS
Drain-Source Voltage	V_{DS}	800	V
Gate-Source Voltage	V_{GS}	30	V
Continuous Drain Current (Steady State)	I_D	12	A
Continuous Drain Current ($T_C=100^\circ C$ Steady State)	I_D	7.7	A
Maximum Pulsed Drain Current, $t_p=10\mu s$	I_{DM}	48	A
Continuous Source Current (Body Diode)	I_S	12	A
Maximum Pulsed Source Current (Body Diode)	I_{SM}	48	A
Single Pulse Avalanche Energy (Note 1)	E_{AS}	702	mJ
Power Dissipation	P_D	40	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to +150	$^\circ C$
Thermal Resistance	θ_{JC}	3.13	$^\circ C/W$
Thermal Resistance	θ_{JA}	62.5	$^\circ C/W$

Note 1: $L=79mH$, $I_{AS}=4.0A$, $V_{DD}=100V$, $R_G=25\Omega$, Initial $T_J=25^\circ C$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=30V, V_{DS}=0$			100	nA
I_{DSS}	$V_{DS}=800V, V_{GS}=0$			1.0	μA
BV_{DSS}	$V_{GS}=0, I_D=250\mu A$	800			V
$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0		4.0	V
V_{SD}	$V_{GS}=0, I_S=12A$			1.4	V
$r_{DS(ON)}$	$V_{GS}=10V, I_D=6.0A$		0.37	0.45	Ω
C_{rss}	$V_{DS}=100V, V_{GS}=0, f=1.0MHz$		9.5		pF
C_{iss}	$V_{DS}=100V, V_{GS}=0, f=1.0MHz$		1,090		pF
C_{oss}	$V_{DS}=100V, V_{GS}=0, f=1.0MHz$		55.2		pF

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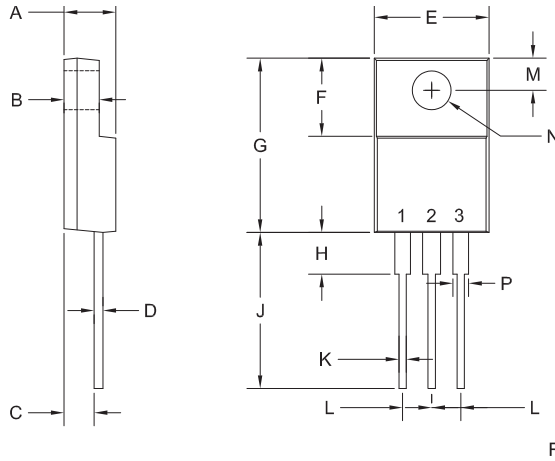


ELECTRICAL CHARACTERISTICS - Continued: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	UNITS
$Q_{g(\text{tot})}$	$V_{DD}=640\text{V}$, $V_{GS}=10\text{V}$, $I_D=12\text{A}$ (Note 2)	52.4	nC
Q_{gs}	$V_{DD}=640\text{V}$, $V_{GS}=10\text{V}$, $I_D=12\text{A}$ (Note 2)	7.6	nC
Q_{gd}	$V_{DD}=640\text{V}$, $V_{GS}=10\text{V}$, $I_D=12\text{A}$ (Note 2)	31.4	nC
$t_{d(\text{on})}$	$V_{DD}=400\text{V}$, $V_{GS}=10\text{V}$, $I_D=12\text{A}$, $R_G=24\Omega$ (Note 2)	21.1	ns
t_r	$V_{DD}=400\text{V}$, $V_{GS}=10\text{V}$, $I_D=12\text{A}$, $R_G=24\Omega$ (Note 2)	44.8	ns
$t_{d(\text{off})}$	$V_{DD}=400\text{V}$, $V_{GS}=10\text{V}$, $I_D=12\text{A}$, $R_G=24\Omega$ (Note 2)	171.2	ns
t_f	$V_{DD}=400\text{V}$, $V_{GS}=10\text{V}$, $I_D=12\text{A}$, $R_G=24\Omega$ (Note 2)	42.5	ns
t_{rr}	$V_{GS}=0$, $I_S=12\text{A}$, $di/dt=100\text{A}/\mu\text{s}$ (Note 2)	430	ns
Q_{rr}	$V_{GS}=0$, $I_S=12\text{A}$, $di/dt=100\text{A}/\mu\text{s}$ (Note 2)	6.5	μC

Note 2: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

TO-220FP CASE - MECHANICAL OUTLINE

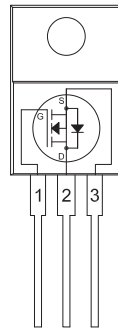


SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.165	0.202	4.20	5.12
B	0.090	0.130	2.30	3.30
C	0.098	0.122	2.50	3.10
D	-	0.031	-	0.80
E	0.382	0.418	9.70	10.63
F	0.238	0.276	6.06	7.00
G	0.583	0.640	14.80	16.25
H	-	0.161	-	4.10
J	0.506	0.543	12.85	13.80
K	0.020	0.031	0.50	0.79
L	0.100		2.54	
M	0.120	0.140	3.05	3.55
N (DIA)	0.116	0.134	2.95	3.40
P	0.039	0.058	1.00	1.47

TO-220FP (REV: R4)

R4

PIN CONFIGURATION



LEAD CODE:

- 1) Gate
- 2) Drain
- 3) Source

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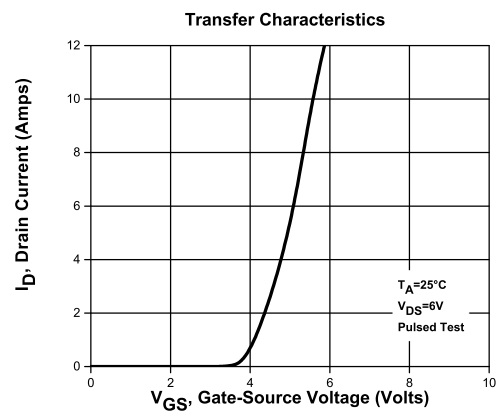
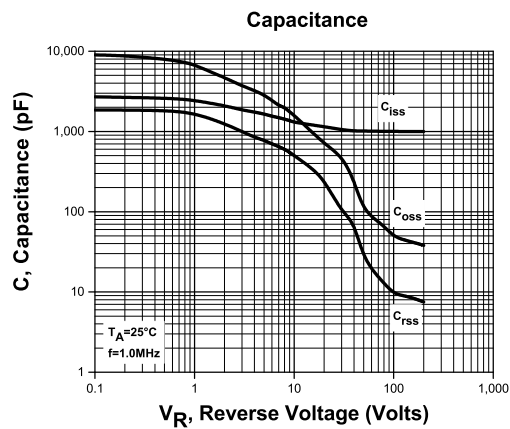
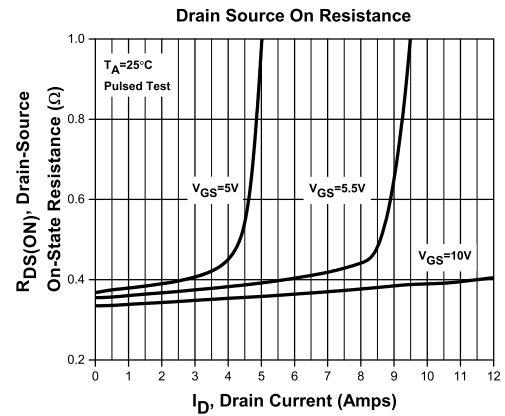
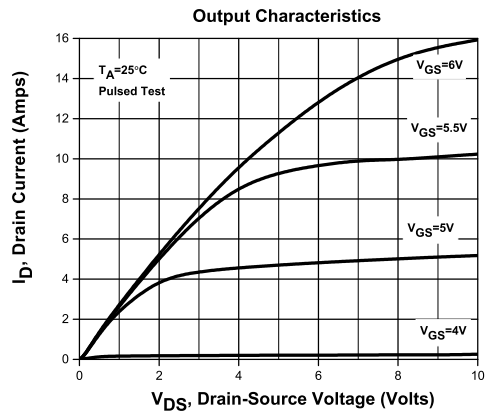
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TYPICAL ELECTRICAL CHARACTERISTICS



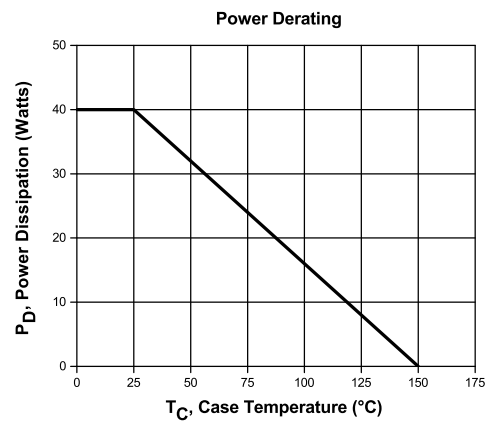
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TYPICAL ELECTRICAL CHARACTERISTICS



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PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

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- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
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- Application notes
- Application and design sample kits
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